



TO-92 Plastic-Encapsulate Transistors

2SC3279 TRANSISTOR (NPN)

FEATURES

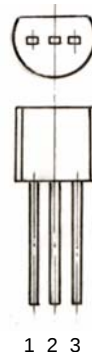
- High DC current gain and excellent h_{FE} linearity
- Low saturation voltage

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	10	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current –Continuous	2	A
P_C	Collector Power Dissipation	750	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}$, $I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}$, $I_B=0$	10			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=0.5\text{A}$	140		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}$, $I_B=100\text{mA}$			0.82	V
Base-emitter voltage	V_{BE}	$I_C=2\text{A}$, $V_{CE}=1\text{V}$			1.5	V
Transition frequency	f_T	$V_{CE}=1\text{V}$, $I_C=0.5\text{A}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$		27		pF

CLASSIFICATION OF h_{FE}

Rank	L	M	N	P
Range	140-240	200-330	300-450	420-600

Typical Characteristics

2SC3279

